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PMEG45A10EPD

45 V, 10 A low VF MEGA Schottky barrier rectifier

16 December 2014

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 10 \text{ A}$
- Reverse voltage: $V_R \leq 45 \text{ V}$
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20 \text{ kHz}$; $T_{sp} \leq 130 \text{ °C}$; square wave	-	-	10	A
V_R	reverse voltage	$T_j = 25 \text{ °C}$	-	-	45	V
V_F	forward voltage	$I_F = 10 \text{ A}$; $t_p \leq 300 \text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ °C}$; pulsed	-	473	540	mV
I_R	reverse current	$V_R = 10 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta = 0.3$; $T_j = 25 \text{ °C}$; pulsed	-	13	30	μA
		$V_R = 45 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta = 0.3$; $T_j = 25 \text{ °C}$; pulsed	-	150	500	μA



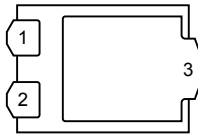
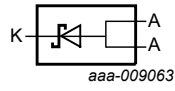
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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 <p>CFP15 (SOT1289)</p>	 <p>aaa-009063</p>
2	A	anode		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG45A10EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG45A10EPD	4510 AAAA

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^\circ\text{C}$		-	45	V
I_F	forward current	$T_{sp} = 125\text{ }^\circ\text{C}$; $\delta = 1$		-	14	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 130\text{ }^\circ\text{C}$; square wave		-	10	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; square wave		-	170	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	[1]	-	0.9	W
			[2]	-	1.2	W
			[3]	-	3	W
T_j	junction temperature			-	150	$^\circ\text{C}$
T_{amb}	ambient temperature			-55	150	$^\circ\text{C}$

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Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	165	K/W
			[1][3]	-	-	120	K/W
			[1][4]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	4	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.

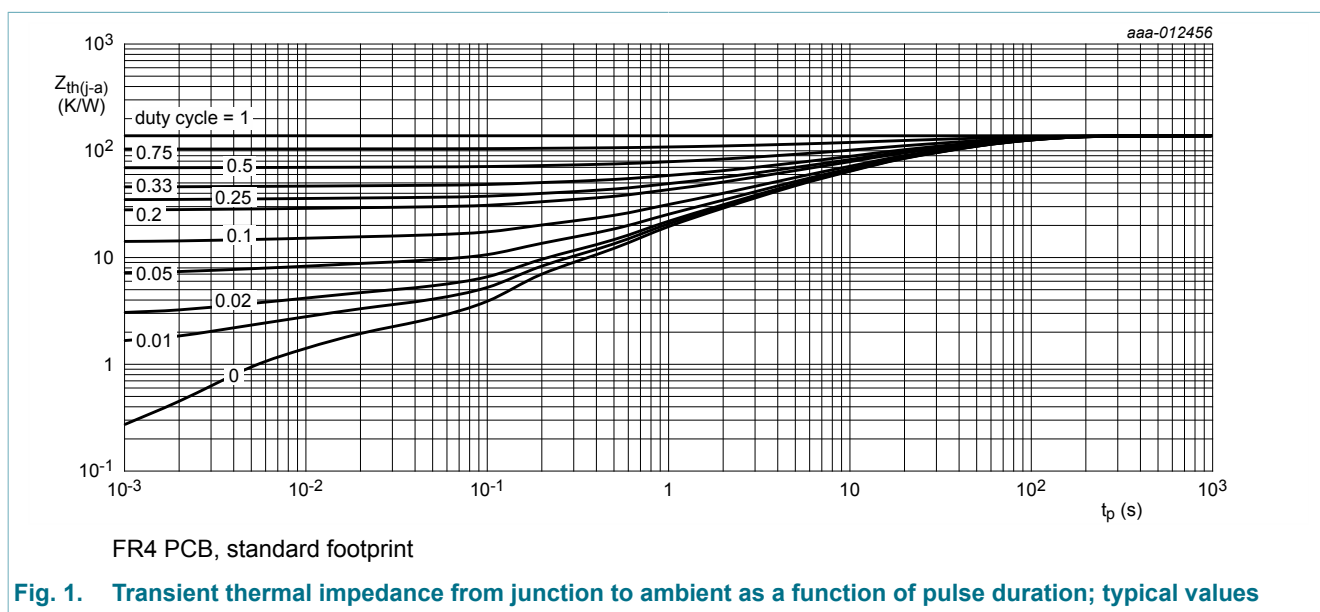


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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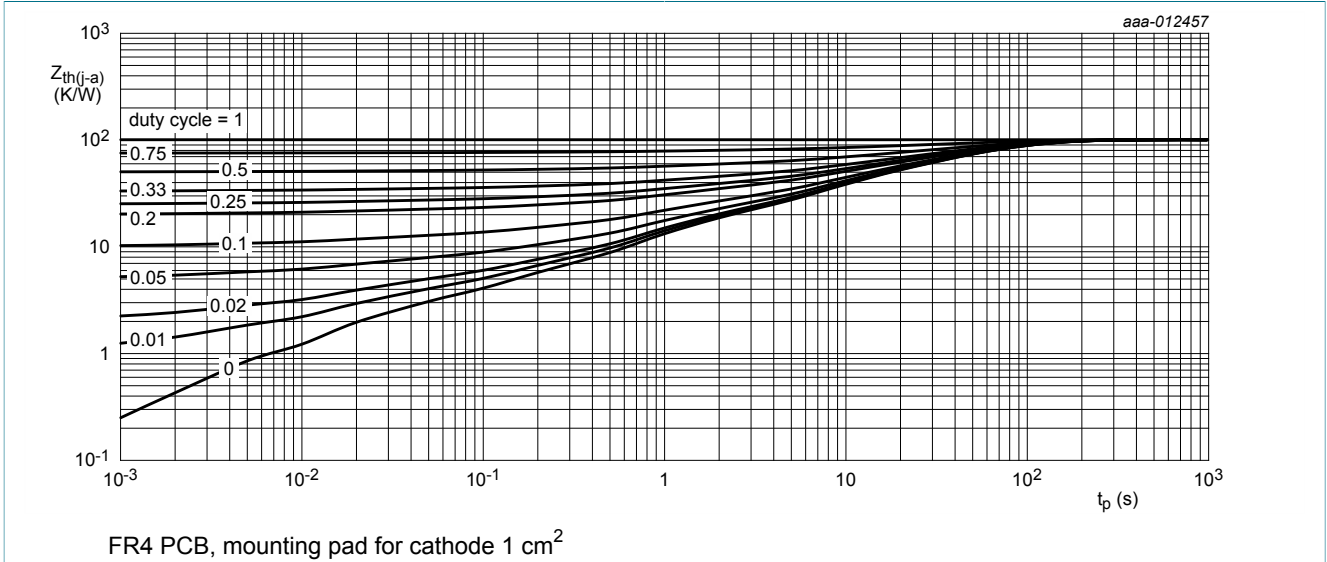


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

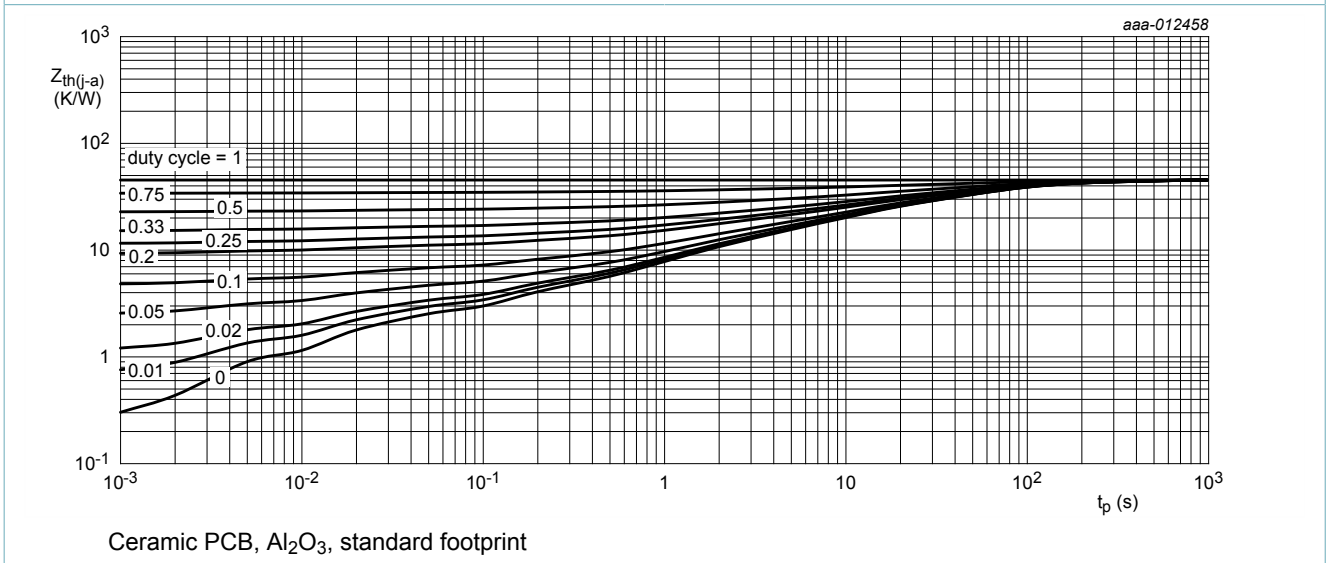


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

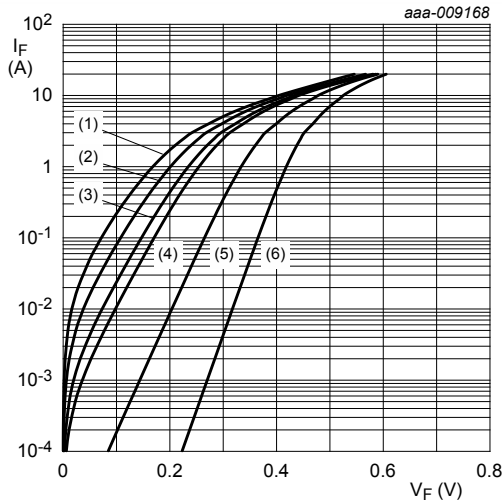
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _F	forward voltage	I _F = 1 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	330	380	mV
		I _F = 2 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	357	-	mV
		I _F = 3 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	377	-	mV
		I _F = 5 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	409	470	mV
		I _F = 10 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	473	540	mV
I _R	reverse current	V _R = 5 V; t _p ≤ 3 ms; δ = 0.3; T _j = 25 °C; pulsed	-	10	-	μA
		V _R = 10 V; t _p ≤ 3 ms; δ = 0.3; T _j = 25 °C; pulsed	-	13	30	μA
		V _R = 30 V; t _p ≤ 3 ms; δ = 0.3; T _j = 25 °C; pulsed	-	36	-	μA
		V _R = 45 V; t _p ≤ 3 ms; δ = 0.3; T _j = 25 °C; pulsed	-	150	500	μA
		V _R = 10 V; t _p ≤ 3 ms; δ = 0.3; T _j = 125 °C; pulsed	-	11	-	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	715	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	240	-	pF
t _{rr}	reverse recovery time ; step recovery	I _F = 0.5 A; I _R = 0.5 A; I _{R(meas)} = 0.1 A; T _j = 25 °C	-	21	-	ns
t _{rr}	reverse recovery time ; ramp recovery	dI _F /dt = 200 A/μs; T _j = 25 °C; I _F = 6 A; V _R = 26 V	-	13	-	ns
V _{(BR)R}	reverse breakdown voltage	I _R = 5 mA; T _j = 25 °C; t _p ≤ 1.2 ms; δ = 0.12; pulsed	45	-	-	V
V _{FRM}	peak forward recovery voltage	I _F = 0.5 A; dI _F /dt = 20 A/μs; T _j = 25 °C	-	317	-	mV

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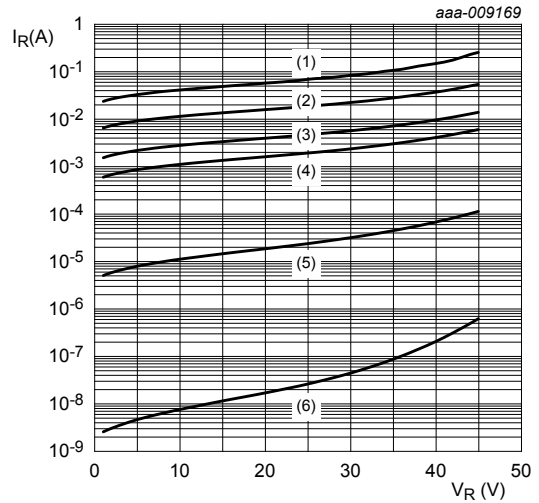
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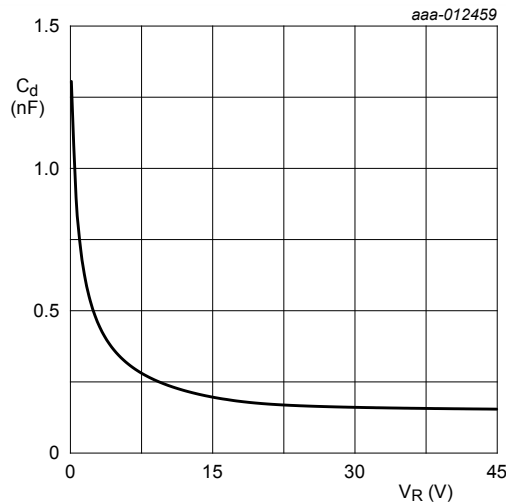
- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 125\text{ }^\circ\text{C}$
- (3) $T_j = 100\text{ }^\circ\text{C}$
- (4) $T_j = 85\text{ }^\circ\text{C}$
- (5) $T_j = 25\text{ }^\circ\text{C}$
- (6) $T_j = -40\text{ }^\circ\text{C}$

Fig. 4. Forward current as a function of forward voltage; typical values (pulsed condition)



- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 125\text{ }^\circ\text{C}$
- (3) $T_j = 100\text{ }^\circ\text{C}$
- (4) $T_j = 85\text{ }^\circ\text{C}$
- (5) $T_j = 25\text{ }^\circ\text{C}$
- (6) $T_j = -40\text{ }^\circ\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values (pulsed condition)



$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values

11. Test information

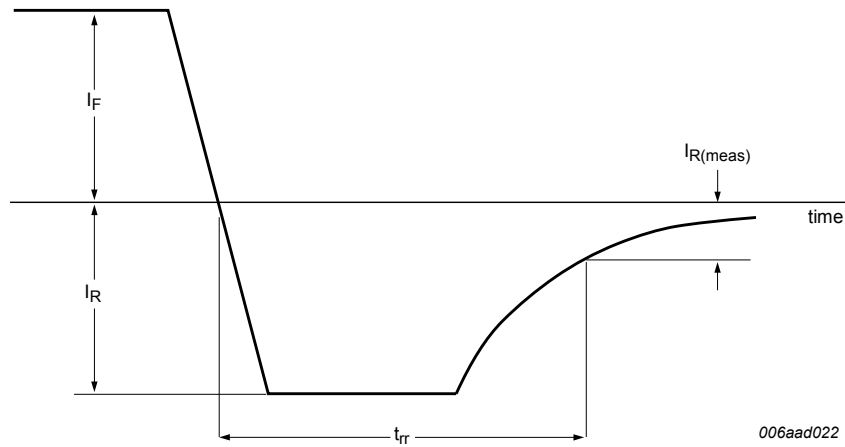


Fig. 7. Reverse recovery definition; step recovery

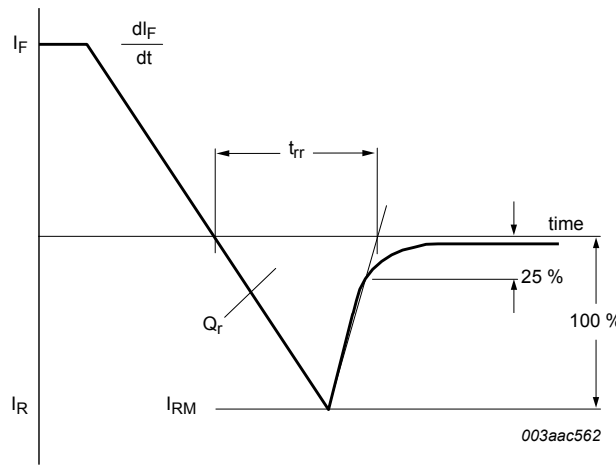


Fig. 8. Reverse recovery definition; ramp recovery

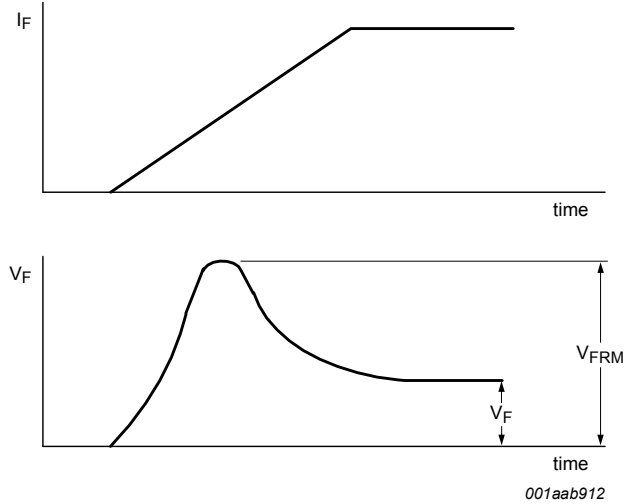


Fig. 9. Forward recovery definition

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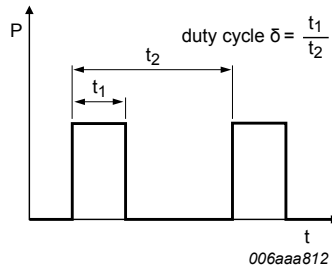


Fig. 10. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:
 $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

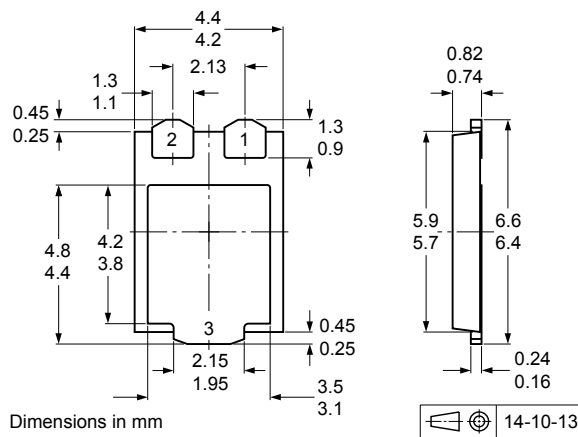


Fig. 11. Package outline CFP15 (SOT1289)

13. Soldering

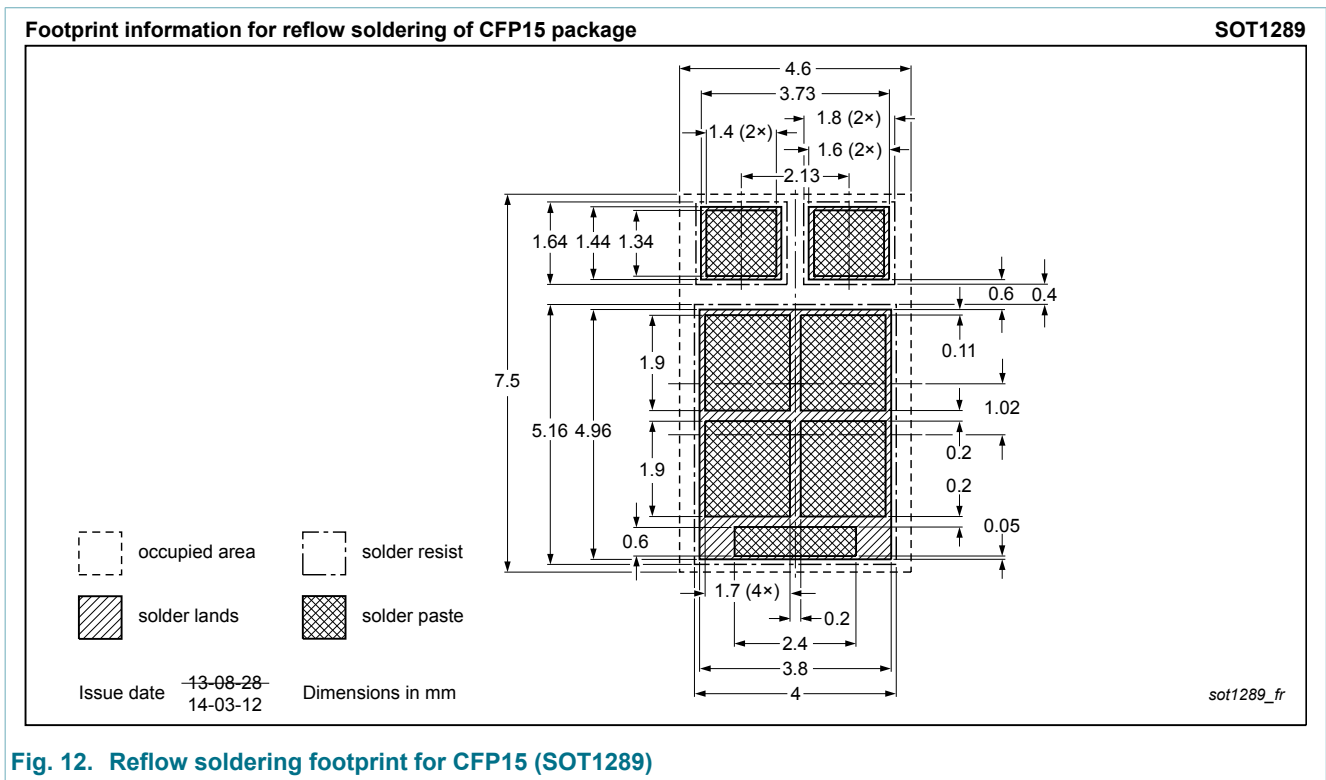


Fig. 12. Reflow soldering footprint for CFP15 (SOT1289)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG45A10EPD v.3	20141216	Product data sheet	-	PMEG45A10EPD v.2
Modifications:	<ul style="list-style-type: none"> Package outline drawing updated 			
PMEG45A10EPD v.2	20140416	Product data sheet	-	PMEG45A10EPD v.1
PMEG45A10EPD v.1	20140217	Objective data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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